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Amendments to the Specification:

Please replace the paragraph beginning at page 14, line 5 as with the following amended paragraph:

Although the invention has been disclosed and illustrated with reference to particular embodiments, the principles involved are susceptible for use in numerous other embodiments, modification and alterations which will be apparent to persons skilled in the art to which the invention pertains. For example, while a top-gate type thin film transistor has been disclosed in the preferred embodiment, the present invention can be applied to a bottom-gate type transistor in which a gate electrode is located below the channel forming region, as shown in Fig. 5. Also, while an anodic oxidation method is preferred for simplicity, other methods such as photolithography may be used to form the gate electrode of the present invention. Further, the present invention can be used in a transistor formed within a single crystalline silicon wafer.

Please add the following new paragraph after the paragraph ending at page 7, line 4:

FIG. 5 shows a bottom-gate type thin film transistor.